CMLT3904E CMLT3904EG\* NPN CMLT3906E CMLT3906EG\* PNP CMLT3946E CMLT3946EG\* NPN/PNP

# **ENHANCED SPECIFICATION** SURFACE MOUNT SILICON





Device is Halogen Free by design

# **ENHANCED SPECIFICATIONS:**

- ♦ BV<sub>CBO</sub> from 40V MIN to 60V MIN (PNP)
- ♦ BV<sub>EBO</sub> from 5.0V MIN to 6.0V MIN (PNP)

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### **DESCRIPTION:**

These CENTRAL SEMICONDUCTOR devices are combinations of dual, enhanced specification transistors in a space saving SOT-563 package, designed for small signal general purpose amplifier and switching applications.

MARKING CODES: CMLT3904E: L04

CMLT3906E: L06 CMLT3946E: L46 C4G CMLT3904EG\*: CMLT3906EG\*: C6G CMLT3946EG\*: 46G

- $\bullet~$  hFE from 60 MIN to 70 MIN (NPN/PNP)
- ◆ VCE(SAT) from 0.3V MAX to 0.2V MAX (NPN) from 0.4V MAX to 0.2V MAX (PNP)

MAXIMUM RATINGS: (T <sub>A</sub> =25°C)	SYMBOL		UNITS	
◆ Collector-Base Voltage	V <sub>CBO</sub>	60	V	
Collector-Emitter Voltage	$V_{CEO}$	40	V	
♦ Emitter-Base Voltage	$V_{EBO}$	6.0	V	
Continuous Collector Current	$I_{\mathbb{C}}$	200	mA	
Power Dissipation (Note 1)	$P_{D}$	350	mW	
Power Dissipation (Note 2)	$P_{D}$	300	mW	
Power Dissipation (Note 3)	$P_{D}$	150	mW	
Operating and Storage Junction Temperature	T <sub>J</sub> , T <sub>stg</sub>	-65 to +150	°C	
Thermal Resistance	ΘιΔ	357	°C/W	

**ELECTRICAL CHARACTERISTICS:** (T<sub>A</sub>=25°C unless otherwise noted)

		<u>NPN</u>	<u>PNP</u>		
TEST CONDITIONS	MIN	TYP	TYP	MAX	UNITS
$V_{CE}$ =30V, $V_{EB}$ =3.0V	-	-	-	50	nA
I <sub>C</sub> =10μA	60	115	90	-	V
I <sub>C</sub> =1.0mA	40	60	55	-	V
I <sub>E</sub> =10μA	6.0	7.5	7.9	-	V
I <sub>C</sub> =10mA, I <sub>B</sub> =1.0mA	-	0.057	0.050	0.100	V
I <sub>C</sub> =50mA, I <sub>B</sub> =5.0mA	-	0.100	0.100	0.200	V
I <sub>C</sub> =10mA, I <sub>B</sub> =1.0mA	0.65	0.75	0.75	0.85	V
I <sub>C</sub> =50mA, I <sub>B</sub> =5.0mA	-	0.85	0.85	0.95	V
V <sub>CE</sub> =1.0V, I <sub>C</sub> =0.1mA	90	240	130	-	
V <sub>CE</sub> =1.0V, I <sub>C</sub> =1.0mA	100	235	150	-	
V <sub>CE</sub> =1.0V, I <sub>C</sub> =10mA	100	215	150	300	
V <sub>CE</sub> =1.0V, I <sub>C</sub> =50mA	70	110	120	-	
V <sub>CE</sub> =1.0V, I <sub>C</sub> =100mA	30	50	55	-	
	V <sub>CE</sub> =30V, V <sub>EB</sub> =3.0V I <sub>C</sub> =10μA I <sub>C</sub> =1.0mA, I <sub>B</sub> =1.0mA I <sub>C</sub> =50mA, I <sub>B</sub> =5.0mA I <sub>C</sub> =10mA, I <sub>B</sub> =5.0mA I <sub>C</sub> =50mA, I <sub>B</sub> =5.0mA V <sub>CE</sub> =1.0V, I <sub>C</sub> =0.1mA V <sub>CE</sub> =1.0V, I <sub>C</sub> =1.0mA V <sub>CE</sub> =1.0V, I <sub>C</sub> =10mA V <sub>CE</sub> =1.0V, I <sub>C</sub> =50mA	V <sub>CE</sub> =30V, V <sub>EB</sub> =3.0V - I <sub>C</sub> =10μA 60 I <sub>C</sub> =1.0mA 40 I <sub>E</sub> =10μA 6.0 I <sub>C</sub> =50mA, I <sub>B</sub> =1.0mA - I <sub>C</sub> =50mA, I <sub>B</sub> =5.0mA - I <sub>C</sub> =50mA, I <sub>B</sub> =5.0mA - V <sub>CE</sub> =1.0V, I <sub>C</sub> =0.1mA 90 V <sub>CE</sub> =1.0V, I <sub>C</sub> =1.0mA 100 V <sub>CE</sub> =1.0V, I <sub>C</sub> =10mA 100 V <sub>CE</sub> =1.0V, I <sub>C</sub> =50mA 70	V <sub>CE</sub> =30V, V <sub>EB</sub> =3.0V	$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$

◆ Enhanced Specification

Notes: 1) Ceramic or aluminum core PC Board with copper mounting pad area of 4.0mm<sup>2</sup>

2) FR-4 Epoxy PC Board with copper mounting pad area of  $4.0 \mathrm{mm}^2$ 

3) FR-4 Epoxy PC Board with copper mounting pad area of 1.4mm<sup>2</sup>

R8 (21-September 2018)

CMLT3904E CMLT3904EG\* NPN CMLT3906E CMLT3906EG\* PNP CMLT3946E CMLT3946EG\* NPN/PNP



ns

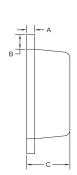
ns

# **ENHANCED SPECIFICATION**

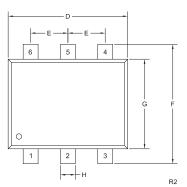
SURFACE MOUNT SILICON **COMPLEMENTARY TRANSISTORS** 

ELECTRICAL CHARACTERISTICS PER TRANSISTOR - Continued: (TA=25°C) UNITS SYMBOL **TEST CONDITIONS** MIN MAX  $V_{CE}$ =20V,  $I_{C}$ =10mA, f=100MHz 300 MHz fΤ  $V_{CB}$ =5.0V,  $I_F$ =0, f=1.0MHz 4.0 pF  $C_{ob}$  $\mathsf{C}_{\mathsf{ib}}$  $V_{BE}$ =0.5V,  $I_{C}$ =0, f=1.0MHz 12 pF 12 h<sub>ie</sub> V<sub>CF</sub>=10V, I<sub>C</sub>=1.0mA, f=1.0kHz 1.0 kΩ h<sub>re</sub>  $V_{CE}$ =10V,  $I_{C}$ =1.0mA, f=1.0kHz 0.1 10 x10<sup>-4</sup> h<sub>fe</sub> V<sub>CF</sub>=10V, I<sub>C</sub>=1.0mA, f=1.0kHz 100 400  $V_{CE}$ =10V,  $I_{C}$ =1.0mA, f=1.0kHz 60 1.0 μS hoe NF  $V_{CF}$ =5.0V,  $I_{C}$ =100 $\mu$ A,  $R_{S}$  =1.0 $k\Omega$ f=10Hz to 15.7kHz 4.0 dΒ V<sub>CC</sub>=3.0V, V<sub>BE</sub>=0.5V, I<sub>C</sub>=10mA, I<sub>B1</sub>=1.0mA 35 ns  $t_d$ 35 V<sub>CC</sub>=3.0V, V<sub>BF</sub>=0.5V, I<sub>C</sub>=10mA, I<sub>B1</sub>=1.0mA  $t_r$ ns

#### **SOT-563 CASE - MECHANICAL OUTLINE**



 $t_S$ 



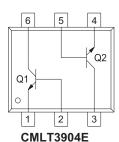
4

Q2

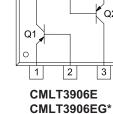
DIMENSIONS						
	INCHES		MILLIMETERS			
SYMBOL	MIN	MAX	MIN	MAX		
Α	0.0027	0.007	0.07	0.18		
В	0.008		0.20			
С	0.017	0.024	0.45	0.60		
D	0.059	0.067	1.50	1.70		
E	0.020		0.50			
F	0.059	0.067	1.50	1.70		
G	0.043	0.051	1.10	1.30		
Н	0.006	0.012	0.15	0.30		
SOT-563 (REV: R2)						

200

50

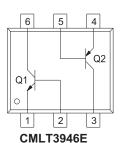


**CMLT3904EG\*** 



 $V_{CC}$ =3.0V,  $I_{C}$ =10mA,  $I_{B1}$ = $I_{B2}$ =1.0mA

V<sub>CC</sub>=3.0V, I<sub>C</sub>=10mA, I<sub>B1</sub>=I<sub>B2</sub>=1.0mA



CMLT3946EG\*

## LEAD CODE:

- 1) Emitter Q1
- 2) Base Q1
- 3) Collector Q2 4) Emitter Q2
- 5) Base Q2
- 6) Collector Q1

R8 (21-September 2018)

<sup>\*</sup> Device is Halogen Free by design



# **OUTSTANDING SUPPORT AND SUPERIOR SERVICES**

#### PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- · Inventory bonding
- · Consolidated shipping options

- Custom bar coding for shipments
- · Custom product packing

#### **DESIGNER SUPPORT/SERVICES**

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free quick ship samples (2<sup>nd</sup> day air)
- · Online technical data and parametric search
- SPICE models
- · Custom electrical curves
- · Environmental regulation compliance
- · Customer specific screening
- · Up-screening capabilities

- Special wafer diffusions
- · PbSn plating options
- · Package details
- · Application notes
- · Application and design sample kits
- Custom product and package development

## REQUESTING PRODUCT PLATING

- 1. If requesting Tin/Lead plated devices, add the suffix "TIN/LEAD" to the part number when ordering (example: 2N2222A TIN/LEAD).
- 2. If requesting Lead (Pb) Free plated devices, add the suffix "PBFREE" to the part number when ordering (example: 2N2222A PBFREE).

# **CONTACT US**

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